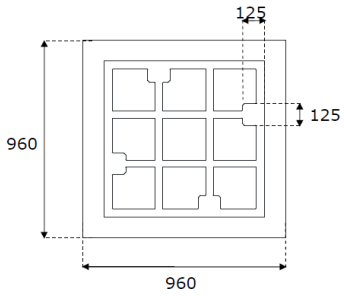


Radiation	Type	Electrodes
Infrared	AlGaAs, DDH	P (anode) up

	<p>typ. dimension (μm)</p> <p>typ. thickness $160 \pm 25 \mu\text{m}$</p> <p>anode - gold alloy, $1.5 \mu\text{m}$</p> <p>cathode - gold alloy $0.5 \mu\text{m}$ structured, 25% covered</p>
Dimensions	

Electrical & Optical Characteristics ($T_a = 25^\circ\text{C}$)

ITEMS	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNIT
Forward Voltage	V_f	$I_f=100\text{mA}$	--	1.35	--	V
Forward Voltage	V_f	$I_f=350\text{mA}$	--	1.7	1.9	V
Reverse Voltage	V_r	$I_r=100\mu\text{A}$	5	--	--	V
Radiant Power*	Φ_e	$I_f=20\text{mA}$	--	4	--	mW
Radiant Power*	Φ_e	$I_f=350\text{mA}$	--	60	--	mW
Switching Time	t_r, t_f	$I_f=20\text{mA}$	--	15; 20	--	ns
Peak Wavelength	λ_p	$I_f=350\text{mA}$	840	850	860	nm
Spectral Bandwidth at 50%	$\Delta\lambda_{0.5}$	$I_f=350\text{mA}$	--	45	--	nm

*Measured on bare chip on TO-18 header

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

ITEMS	SYMBOL	RATINGS	UNIT
Forward DC Current	I_f	500	mA



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.